	Type	Hits	Search Text	DBs
1	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT
2	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT
3	BRS	0	"light emitting device" and semiconductor and "p-type layer" and "ohmic layer" and "reflector layer"	USPAT
4	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "reflector layer"	USPAT
5	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "n-type layer"	USPAT
6	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPAT
7	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "reflector layer"	USPAT
8	BRS	13	"light emitting device" and semiconductor and "ohmic layer"	USPAT
9	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "mirror layer"	USPAT
10	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "reproducer layer"	USPAT
11	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT
12	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicator layer"	USPAT
13	BRS	0	"light emitting diode" and semiconductor and "ohmic layer" and "p-type layer" and "replicate layer"	USPAT

	Type	Hits	Search Text	DBs
14	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "replicate layer"	USPAT
15	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "replicate"	USPAT
16	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "mirror"	USPAT
17	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer" and "reproduce"	USPAT
18	BRS	0	"light emitting divice" and "semiconductor layer" and "ohmic layer" and "p-type layer"	USPAT
19	BRS	0	"light emitting divice" and "ohmic layer" and "p-type layer"	USPAT
20	BRS	0	"light emitting divice" and semiconductor and "ohmic layer" and "p-type layer"	USPAT
21	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer"	USPAT
22	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and "p-type layer" and replicator	USPAT
23	BRS	1	"light emitting device" and semiconductor and "ohmic layer" and p-type adj layer	USPAT
24	BRS	0	"light emitting device" and semiconductor and "ohmic layer" and p-type adj layer and replicator	USPAT
25	BRS	0	"light emitting device" and semiconductor adj layer and "ohmic layer" and p-type adj layer	USPAT
26	BRS	1	"light emitting device" and semiconductor adj layers and "ohmic layer" and p-type adj layer	USPAT

	Type	Hits	Search Text	DBs
27	BRS	1	"light emitting device" and semiconductor adj layers and "ohmic layer" and p-type adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB
28	BRS	13035	"light emitting device"	USPAT; EPO; JPO; DERWENT; IBM_TDB
29	BRS	671	"light emitting device" and semiconductor adj layers	USPAT; EPO; JPO; DERWENT; IBM_TDB
30	BRS	125	"light emitting device" and semiconductor adj layers and p-type adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB
31	BRS	87	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB
32	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB
33	BRS	2202163	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector layer	USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
34	BRS	707	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector layer and "ohmic layer"	USPAT; EPO; JPO; DERWENT; IBM_TDB
35	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and reflector adj layer and "ohmic layer"	USPAT; EPO; JPO; DERWENT; IBM_TDB
36	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and "ohmic layer"	USPAT; EPO; JPO; DERWENT; IBM_TDB
37	BRS	2	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflect	USPAT; EPO; JPO; DERWENT; IBM_TDB
38	BRS	9	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror	USPAT; EPO; JPO; DERWENT; IBM_TDB
39	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproducer	USPAT; EPO; JPO; DERWENT; IBM_TDB
40	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproduce	USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
41	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicator	USPAT; EPO; JPO; DERWENT; IBM_TDB
42	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicate	USPAT; EPO; JPO; DERWENT; IBM_TDB
43	BRS	0	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and replicate	USPAT; EPO; JPO; DERWENT; IBM_TDB
44	BRS	0	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reproduce	USPAT; EPO; JPO; DERWENT; IBM_TDB
45	BRS	36	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic	USPAT; EPO; JPO; DERWENT; IBM_TDB
46	BRS	13	"light emitting diode" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and mirror	USPAT; EPO; JPO; DERWENT; IBM_TDB
47	BRS	0	5351255.pn. and nickel and silver	USPAT
48	BRS	0	5351255.pn. and nickel	USPAT
49	BRS	1	5351255.pn.	USPAT

	Type	Hits	Search Text	DBs
50	BRS	1	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
51	BRS	12	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and contact adj resistance	USPAT; EPO; JPO; DERWENT; IBM_TDB
52	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "GaN"	USPAT
53	BRS	19	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and "GaN"	USPAT; EPO; JPO; DERWENT; IBM_TDB
54	BRS	1	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
55	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and "light loss"	USPAT; EPO; JPO; DERWENT; IBM_TDB
56	BRS	0	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorbtion	USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
57	BRS	4	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorb	USPAT; EPO; JPO; DERWENT; IBM_TDB
58	BRS	12	"light emitting device" and semiconductor adj layers and p-type adj layer and n-type adj layer and ohmic and absorption	USPAT; EPO; JPO; DERWENT; IBM_TDB
59	BRS	21	"light emitting device" and "GaN" and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
60	BRS	21	"light emitting device" and "GaN" and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
61	BRS	3	"light emitting device" and "GaN" and "ohmic" and "multi layer" and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
62	BRS	11	"light emitting device" and "GaN" and "ohmic" and reflectivity	USPAT; EPO; JPO; DERWENT; IBM_TDB
63	BRS	1	5351255.PN.	USPAT
64	BRS	0	5351255.PN. AND 5585648.PN. AND 5932896.PN. AND 6190937.PN. AND 6057565.PN. AND 5990500.PN.	USPAT
65	BRS	6	5351255.PN. OR 5585648.PN. OR 5932896.PN. OR 6190937.PN. OR 6057565.PN. OR 5990500.PN.	USPAT

	Type	Hits	Search Text	DBs
66	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and "ohmic layer" and "reflector layer"	USPAT; EPO; JPO; DERWENT; IBM_TDB
67	BRS	4	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	USPAT; EPO; JPO; DERWENT; IBM_TDB
68	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and reflector	EPO; JPO; DERWENT; IBM_TDB
69	BRS	0	"light emitting device" and "p-type layer" and "n-type layer" and ohmic and reflector	EPO; JPO; DERWENT; IBM_TDB
70	BRS	0	"light emitting device" and semiconductor adj material and "p-type layer" and "n-type layer" and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB
71	BRS	0	"light emitting device" and semiconductor adj material and "p-type " and "n-type " and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB
72	BRS	0	"light emitting device" and semiconductor adj material and "p-type" and "n-type" and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB
73	BRS	0	"light emitting device" and semiconductor adj material and "multi layers" and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
74	BRS	0	"light emitting device" and semiconductor and "multi layers" and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB
75	BRS	0	"light emitting device" and semiconductor and "multi layers" and mirror	EPO; JPO; DERWENT; IBM_TDB
76	BRS	0	"light emitting device" and "multi layers" and mirror and ohmic	EPO; JPO; DERWENT; IBM_TDB
77	BRS	0	"light emitting device" and "multi layers" and ohmic	EPO; JPO; DERWENT; IBM_TDB
78	BRS	8576	"light emitting device"	EPO; JPO; DERWENT; IBM_TDB
79	BRS	6	"light emitting device" and ohmic adj layer	EPO; JPO; DERWENT; IBM_TDB
80	BRS	0	"light emitting device" and ohmic adj layer and reflector	EPO; JPO; DERWENT; IBM_TDB
81	BRS	0	"light emitting device" and ohmic adj layer and mirror	EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
82	BRS	1	"light emitting device" and ohmic and mirror	EPO; JPO; DERWENT; IBM_TDB
83	BRS	2	5585648.pn.	EPO; JPO; DERWENT; IBM_TDB
84	BRS	1	5585648.pn.	USPAT
85	BRS	0	barrier adj layer and (HgSe and mercury adj selenium)	USPAT
86	BRS	16	barrier adj layer and (HgSe or mercury adj selenium)	USPAT
87	BRS	0	barrier adj layer near (HgSe or mercury adj selenium)	USPAT
88	BRS	1	barrier adj layer same (HgSe or mercury adj selenium)	USPAT
89	BRS	35	ohmic adj contact adj layer and thickness near "200"	USPAT
90	BRS	1	ohmic adj contact adj layer and thickness near "200" adj angstroms	USPAT
91	BRS	101	ohmic adj contact adj layer and thickness near ("200" adj angstroms or 0.1 microns)	USPAT
92	BRS	70	ohmic adj contact adj layer and thickness near ("200" adj angstroms or 0.2 microns)	USPAT
93	BRS	24	ohmic adj contact adj layer near thickness	USPAT
94	BRS	31	ohmic adj contact adj layer near thickness	USPAT
95	BRS	0	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and reflector near layer and "p contact" and "n contact"	USPAT; JPO
96	BRS	1	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and reflector near layer	USPAT; JPO
97	BRS	1	"5744857".PN.	USPAT
98	BRS	1	"5925898".PN.	USPAT

	Type	Hits	Search Text	DBs
99	BRS	11	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and (reflector or gold or "Au") near layer	USPAT; JPO
100	BRS	29	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and (reflector or gold or "Au" or metal) near layer	USPAT; JPO
101	BRS	16	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and (aluminum or "Al" or copper or "Cu" or rhodium or "Rh" or palladium or "Pd") near layer	USPAT; JPO
102	BRS	33	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and (aluminum or "Al" or copper or "Cu" or rhodium or "Rh" or palladium or "Pd" or reflector or metal or gold or "Au") near layer	USPAT; JPO
103	BRS	0	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and (aluminum or "Al" or copper or "Cu" or rhodium or "Rh" or palladium or "Pd" or reflector or metal or gold or "Au") near layer and 5959307.pn.	USPAT; JPO
104	BRS	0	("light emitting device" or "LED") and p-type near layer and n-type near layer and ohmic near layer and 5959307.pn.	USPAT; JPO
105	BRS	0	("light emitting device" or "LED") and ohmic near layer and 5959307.pn.	USPAT; JPO
106	BRS	1	("light emitting device" or "LED") and ohmicand 5959307.pn.	USPAT; JPO
107	BRS	1	("light emitting device" or "LED") and ohmic and p adj type and n adj type and 5959307.pn.	USPAT; JPO
108	BRS	1430	("light emitting device" or "LED") and ohmic and p adj type and n adj type	USPAT; JPO
109	BRS	0	("light emitting device" or "LED") and ohmic and p adj type and n adj type and refector	USPAT; JPO

	Type	Hits	Search Text	DBs
110	BRS	146	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflector	USPAT; JPO
111	BRS	29	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflector near (layer or film)	USPAT; JPO
112	BRS	1	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflector near (thickness)	USPAT; JPO
113	BRS	28	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflector with (thickness)	USPAT; JPO
114	BRS	1	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity with "75"	USPAT; JPO
115	BRS	120	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity	USPAT; JPO
116	BRS	3	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity and metal$8 near reflector	USPAT; JPO
117	BRS	8	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity and (metal$8 or aold) with reflector	USPAT; JPO
118	BRS	38	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity and (metal$8 or aold) with reflect$3	USPAT; JPO
119	BRS	41	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity and (metal$8 or gold) with reflect$3	USPAT; JPO
120	BRS	38	("light emitting device" or "LED") and ohmic and p adj type and n adj type and reflectivity and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO
121	BRS	12	257/98 and ohmic and p adj type and n adj type and reflectivity and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO

	Type	Hits	Search Text	DBs
122	BRS	5	257/99 and ohmic and p adj type and n adj type and reflectivity and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO
123	BRS	16	257/99 and ohmic and p adj type and n adj type and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO
124	BRS	14	257/99 and ohmic near contact and p adj type and n adj type and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO
125	BRS	4	(257/700 or 257/742 or 257/743 or 257/744 or 257/745) and ohmic near contact and p adj type and n adj type and (metal$8 or gold) with reflect$3 and thickness	USPAT; JPO
126	BRS	32	(257/98 or 257/99) and ohmic near contact and p adj type and n adj type and reflect$3 with thickness	USPAT; JPO
127	BRS	67	(257/98 or 257/99) and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness	USPAT; JPO
128	BRS	18	(257/98 or 257/99) and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness not ((257/98 or 257/99) and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness)	USPAT; JPO
129	BRS	85	(257/98 or 257/99) and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness	USPAT; JPO

	Type	Hits	Search Text	DBs
130	BRS	314	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness	USPAT; JPO
131	BRS	0	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) with reflect$3 and reflectivity near "75"	USPAT; JPO
132	BRS	0	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) with (reflect$3 or layer or film) and reflectivity near "75"	USPAT; JPO
133	BRS	0	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) with (reflect$3 or layer or film) and reflectivity near "80"	USPAT; JPO
134	BRS	0	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) with (reflect$3 or layer or film) and @reflectivity>=75	USPAT; JPO

	Type	Hits	Search Text	DBs
135	BRS	0	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same (reflect$3 or layer or film) and @reflectivity>=75	USPAT; JPO
136	BRS	0	(diode or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same (reflect$3 or layer or film) and @reflectivity>=75	USPAT; JPO
137	BRS	36	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflect$3 and thickness	USPAT; JPO
138	BRS	3	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) and reflect$5 near "%" and thickness	USPAT; JPO
139	BRS	624	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) and reflect$5 and thickness	USPAT; JPO

	Type	Hits	Search Text	DBs
140	BRS	148	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) and reflectivity	USPAT; JPO
141	BRS	14	((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflect$3 and reflectivity	USPAT; JPO
142	BRS	120	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflect$3 and thickness	USPAT
143	BRS	15	(("light emitting" near (diode or device)) or laser or "LED") and (metal$8 or ohmic) near contact near reflect$3 and thickness	USPAT
144	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and (metal$8 or ohmic) near contact near @reflect$3>=75 and thickness	USPAT
145	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and (metal$8 or ohmic) near contact and @reflectivity>=75 and thickness	USPAT
146	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and (metal$8 or ohmic) near contact and @reflectivity>=75	USPAT
147	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and (metal$8 or ohmic) near contact and @reflectivity>=75$2	USPAT
148	BRS	0	(("light emitting" near (diode or device)) or diode or laser or "LED") and (metal$8 or ohmic) near contact and @reflectivity>=75$2	USPAT

	Type	Hits	Search Text	DBs
149	BRS	0	@reflectivity>=75$2	USPAT
150	BRS	0	(("light emitting" near (diode or device)) or diode or laser or "LED") and (metal$8 or ohmic) near contact and reflectivity near "75" adj ("%" or percent)	USPAT
151	BRS	2	(("light emitting" near (diode or device)) or diode or laser or "LED") and (metal$8 or ohmic) near contact and reflectivity near 75$2	USPAT
152	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 75$2 and thickness	USPAT
153	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 80$2 and thickness	USPAT
154	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 90$2 and thickness	USPAT
155	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 95$2 and thickness	USPAT

	Type	Hits	Search Text	DBs
156	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 95$2	USPAT
157	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 90$2	USPAT
158	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 85$2	USPAT
159	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 80$2	USPAT
160	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 75$2	USPAT
161	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 75$5	USPAT

	Type	Hits	Search Text	DBs
162	BRS	0	(("light emitting" near (diode or device)) or laser or "LED") and ohmic near contact and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) near reflectivity near 75$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
163	BRS	0	6169294.pn. and ((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type and (metal$8 or metal or gold or "Au" or "Al" or aluminum or "Cu" or copper or "Rh" or rhodium or "Pd" or palladium or "Ag" or silver) same reflect$3 and thickness	USPAT
164	BRS	1	6169294.pn. and ((("light emitting" or laser) adj diode) or "LED") and ohmic near contact and p adj type and n adj type	USPAT